RBHM

CUSTOMER		NO. MMST8098		
SUBJECT SOT-23 TRANSISTOR, NPN , SILICON		PAGE 1 of 2 DATE January 14, 1987		
ABSOLUTE MAXIMUM RATINGS: (Ta = 25°C)				
Collector-Base Voltage	V _{CB0}	60 V		
Collector-Emitter Voltage	VCEO	60 V		
Emitter-Base Voltage	VEBO	6 V		
Collector Current	IC	200 mA		
Power Dissipation-Free Air	PD	200 mW		
Power Dissipation-Ceramic Substrate	Р _D	350 mW		
Operating and Storage Junction Temperatur	e Tj, T _{stg}	-55 to 150 °C		
Solder Temperature (10 seconds)	-	260 °C		
$ \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \begin{array}{c} \end{array}\\ \end{array}\\ \end{array}\\ \end{array}\\ \end{array}\\ \end{array} \\ \begin{array}{c} \end{array}\\ \end{array} \\ \begin{array}{c} \end{array}\\ \end{array} \\ \begin{array}{c} \end{array}\\ \end{array} \\ \begin{array}{c} \end{array}\\ \end{array}$ \left(\begin{array}{c} \end{array}\\ \end{array} \left(\begin{array}{c} \end{array} \left(\begin{array}{c} \end{array} \left(\begin{array}{c} \end{array} \left(\end{array}) \left(\begin{array}{c} \end{array} \left(\end{array}) \left(\end{array}) \left(\begin{array}{c} \end{array} \left(\end{array}) () () () () () () () () () () () () ()	2.90 ± 2.90 ± 1 4 -0.95 + 0 -1.90 ±			
THE JAPAN	ESE STYLE SC	-59 PACKAGE		
MARKING:		GING: BULK, 500 per BAG MAGAZINES OF 50 EACH 8mm T&R, T-146 3K/REEL 8mm T&R, T-147 3K/REEL 8mm T&R, T-246 10K/REEL 8mm T&R, T-247 10K/REEL		
REMARKS: PROCESS: <u>C-22</u> Thermal Re	esistance R _O	$JA = \frac{625}{FREE AIR, TA} = 25^{\circ}C$		
ROHM ELECTRONICS 3034 Owen Drive, Antioch, TN 37013 TEL:(615)641-2020 FAX:(615)641-2022	APPROVA ARD 10/12/8	CHECK DESIGN		
F 50-4	<i></i>	MASI		

ROHM

CUSTOMER		NO. MMST8098		
SUBJECT		PAGE 2 of 2		
TRANSISTOR, NPN , SILICON SOT-23		DATE January 14, 1987		
ELECTRICAL CHARACTERISTICS: (Ta = 25°C Unles	s Otherw	ise Specified	1)	
PARAMETER TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{CB0} I _C = 100 μA	60			v
BV _{CEO} I _C = 10 mA	60			V
BV_{EBO} I _E = 10 μ A	6			V
I_{CBO} $V_{CB} = 60 V$		2.0	100	nA
I_{CEO} $V_{CE} = 60$ V		1.5	100	nA
I_{EBO} $V_{EB} = 6 V$		1.0	100	'nA
h_{FE} I _C = 1.0 mA, V_{CE} = 5.0 V	100		300	
h_{FE} I _C = 10 mA, V _{CE} = 5.0 V	100			
h_{FE} I _C = 100 mA, V _{CE} = 5.0 V	75			
$V_{CE}(SAT)$ I _C = 100 mA, I _B = 5.0 mA			0.4	v
$V_{CE(SAT)}$ I _C = 100 mA, I _B = 10 mA			0.3	v
$V_{BE(ON)}$ I _C = 1.0 mA, V_{CE} = 5.0 V	0.5		0.7	v
f_T I _C = 10 mA, V _{CE} = 5.0 V, f= 100MHz	150	350		MHz
$V_{CB} = 5.0 V$, $I_E = 0$, $f = 1.0 MHz$			6.0	pF
$V_{BE} = 5.0 V$, $I_{C} = 0$, $f = 1.0 MHz$			25	pF
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